优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

0755-83047638
ysbdt@szyoushang.cn
www.szyoushang.cn

企业微信二维码

企业QQ二维码

Features

- BV_{CEO} > -400V
- BV_{ECO} > -6V
- I_C = -0.2A Continuous Collector Current
- Low Saturation Voltage $V_{CE(SAT)}$ < -220mV @ -100mA
- h_{FE} Min 100 @ -200mA
- 1.5W Power Dissipation
- Complementary NPN Type: NK-ZXTN08400BFF

Mechanical Data

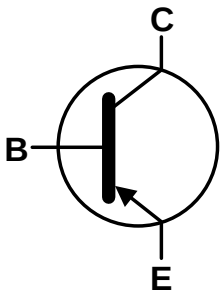
- Case: SOT23F
- Case Material: Molded Plastic. “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 e3
- Weight: 0.012 grams (Approximate)

Description

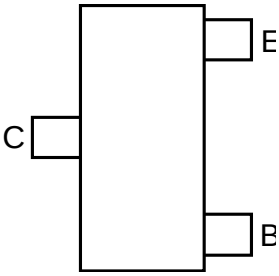
This PNP transistor is designed for applications requiring high blocking voltage. The SOT23F package is pin compatible with the industry standard SOT23 footprint but offers lower profile and higher dissipation for applications where power density is of utmost importance.

SOT23F

Top View



Device symbol



Top View
Pin Configuration

Absolute Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-400	V
Collector-Emitter Voltage	V_{CEO}	-400	V
Emitter-Collector Voltage (Reverse Blocking)	V_{ECO}	-6	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-0.2	A
Peak Pulse Current	I_{CM}	-1	A
Base Current	I_B	-0.2	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

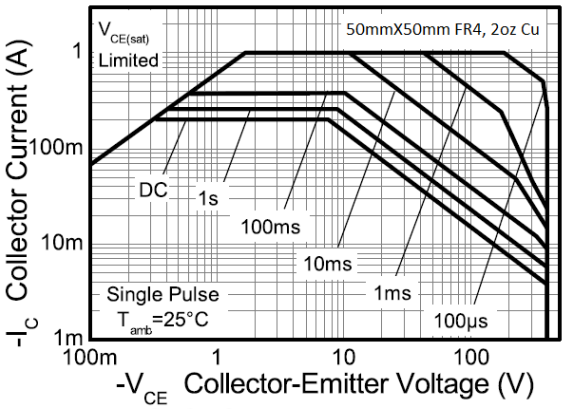
Characteristic		Symbol	Value	Unit
Power Dissipation Linear Derating Factor	(Note 5)	P_D	0.84 6.72	W mW/°C
	(Note 6)		1.34 10.72	
	(Note 7)		1.50 12.0	
	(Note 8)		2.0 16.0	
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	149	°C/W
	(Note 6)		93	
	(Note 7)		83	
	(Note 8)		60	
Thermal Resistance, Junction to Lead	(Note 9)	$R_{\theta JL}$	43.8	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

ESD Ratings (Note 10)

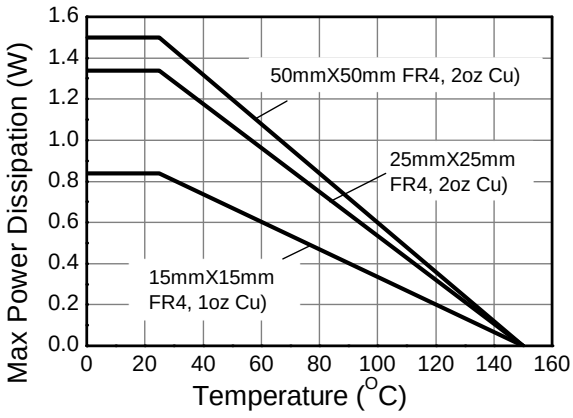
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

Notes:
5. For a device mounted with the exposed collector pad on 15mm x 15mm 1oz copper that is on a single-sided 1.6mm FR-4 PCB; device is measured under still air conditions whilst operating in a steady-state.
6. Same as Note 5, except the device is mounted on 25mm x 25mm 2oz copper.
7. Same as Note 5, except the device is mounted on 50mm x 50mm 2oz copper.
8. Same as Note 7, whilst measured at t < 5 seconds.
9. Thermal resistance from junction to solder-point (at the end of the collector lead).
10. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

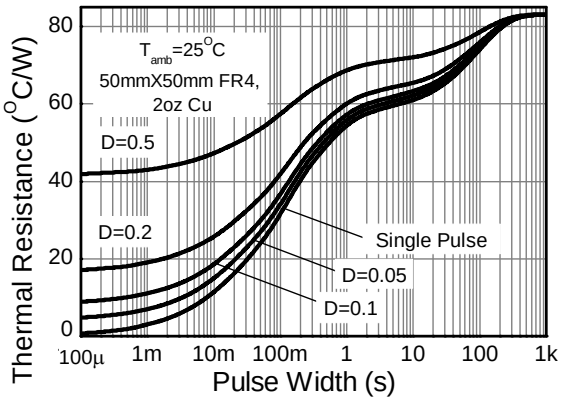
Thermal Characteristics and Derating Information



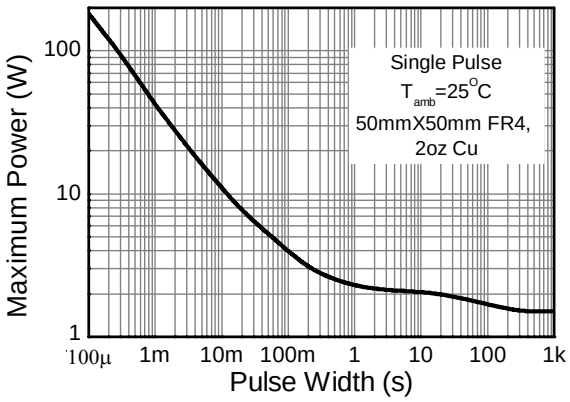
Safe Operating Area



Derating Curve



Transient Thermal Impedance



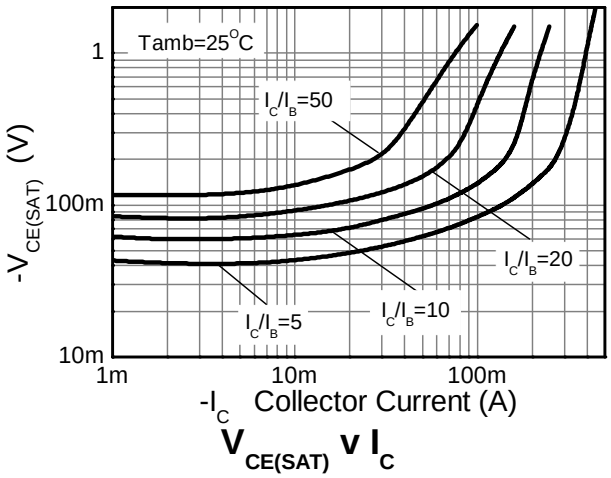
Pulse Power Dissipation

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

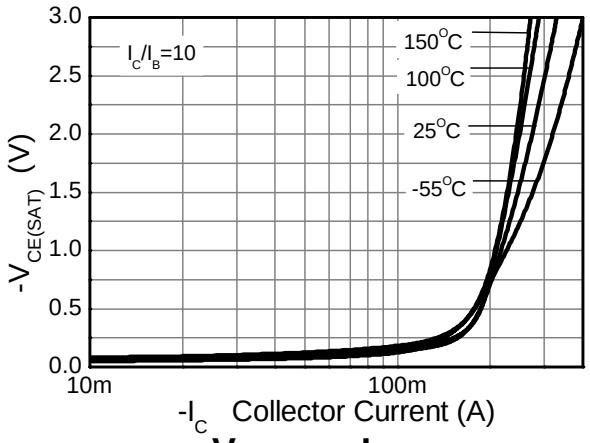
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	BV_{CBO}	-400	-500	—	V	I_C = -100μA
Collector-Emitter Breakdown Voltage (Base Open) (Note 11)	BV_{CEO}	-400	-480	—	V	I_C = -10mA
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.1	—	V	I_E = -100μA
Emitter-Collector Breakdown Voltage (Reverse Blocking)	BV_{ECX}	-6	-8.2	—	V	I_E = -100μA; R_{BC} < 1kΩ or 0.25V < V_{BC} < -0.25V
Emitter-Collector Breakdown Voltage (Base Open)	BV_{ECO}	-6	-8.6	—	V	I_E = -100μA
Collector-Base Cut-Off Current	I_{CBO}	—	< -1 —	-50 -20	nA μA	V_{CB} = -320V V_{CB} = -320V, T_A = +100°C
Emitter-Base Cut-Off Current	I_{EBO}	—	< -1	-50	nA	V_{EB} = -5.6V
ON CHARACTERISTICS (Note 11)						
Static Forward Current Transfer Ratio	h_{FE}	100 100 100	220 200 200	— 300 —	—	I_C = -1mA, V_{CE} = -5V I_C = -50mA, V_{CE} = -5V I_C = -200mA, V_{CE} = -10V
Collector-Emitter Saturation Voltage	$V_{CE(SAT)}$	—	-10 -95 -140 -140	-145 -125 -220 -190	mV	I_C = -20mA, I_B = -1mA I_C = -50mA, I_B = -5mA I_C = -100mA, I_B = -10mA I_C = -200mA, I_B = -40mA
Base-Emitter Saturation Voltage	$V_{BE(SAT)}$	—	-810	-900	mV	I_C = -200mA, I_B = -40mA
Base-Emitter On Voltage	$V_{BE(ON)}$	—	-705	-800	mV	I_C = -200mA, V_{CE} = -10V
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f_T	50	70	—	MHz	I_C = -20mA, V_{CE} = -20V, f = 20MHz
Output Capacitance	C_{OBO}	—	12.9	20	pF	V_{CB} = -20V, f = 1MHz
Delay Time	t_D	—	95	—	ns	V_{CC} = -100V, I_C = -100mA, I_{B1} = -I_{B2} = -20mA
Rise Time	t_R	—	73.8	—	ns	
Storage Time	t_S	—	1790	—	ns	
Fall Time	t_F	—	153.8	—	ns	

Note: 11. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

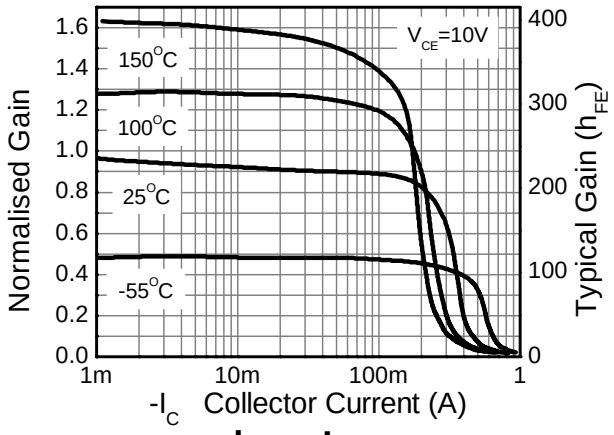
Typical Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)



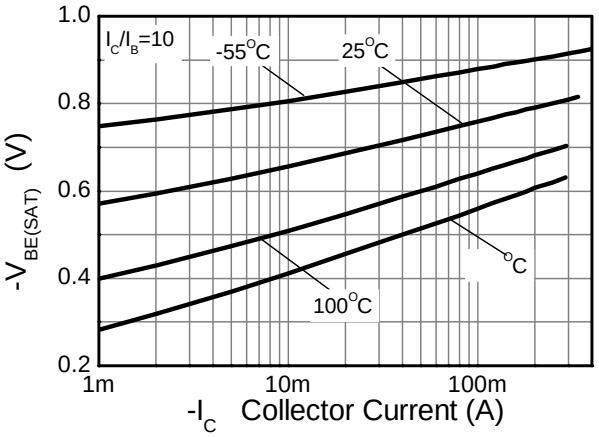
$V_{CE(SAT)}$ v I_C



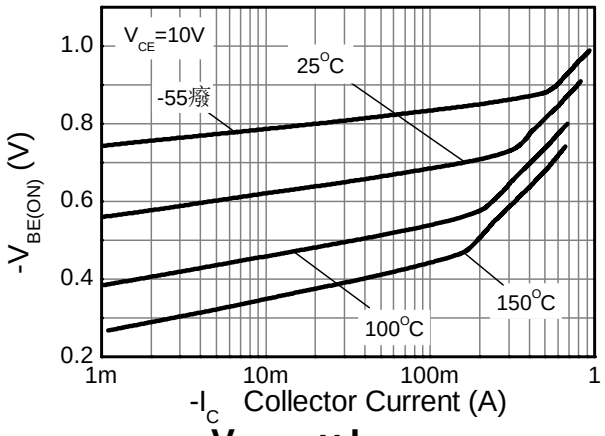
$V_{CE(SAT)}$ v I_C



h_{FE} v I_C



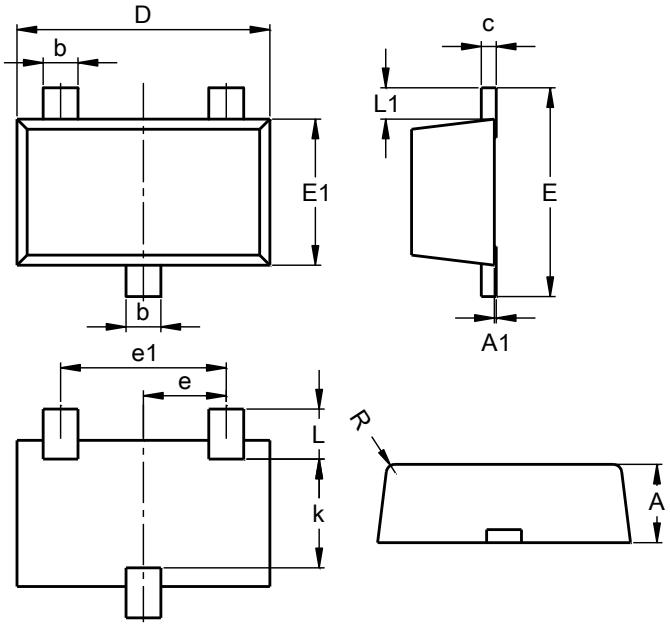
$V_{BE(SAT)}$ v I_C



$V_{BE(ON)}$ v I_C

Package Outline Dimensions

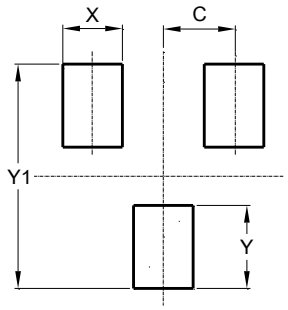
SOT23F



SOT23F			
Dim	**Min**	**Max**	**Typ**
A	0.80	1.00	0.90
A1	0.00	0.10	0.01
b	0.35	0.50	0.44
c	0.10	0.20	0.16
D	2.80	3.00	2.90
e	0.95 REF		
e1	1.90 REF		
E	2.30	2.50	2.40
E1	1.50	1.70	1.65
k	1.20	-	-
L	0.30	0.65	0.50
L1	0.30	0.50	0.40
R	0.05	0.15	-
All Dimensions in mm			

Suggested Pad Layout

SOT23F



Dimensions	Value (in mm)
C	0.95
X	0.80
Y	1.110
Y1	3.000

Note: For high voltage applications, the appropriate industry sector guidelines should be considered with regards to voltage spacing between terminals.